Document Number: ITEH38009C6 Preliminary Datasheet V1.0

9W,28V Plastic RF LDMOS Transistor

Description

The ITEH38009C6 is a 9-watt, highly rugged, LDMOS transistor, designed for any general applications at frequencies up to 3.8GHz, in 10*6mm QFN plastic package, supporting surface mounted on PCB through high density grounding vias.

It is part of low power general purpose plastic LDMOS with pin to pin compatibility.

• Typical 3.3-3.6 GHz Class AB RF Performance (On Innogration fixture with device soldered).

VDS=28V, IDQ=70mA, Vgs=2.74V, Pout=29dBm, 100MHz NR

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Freq	Gain (dB)	EFF (%)	ACPR (dBc)
(MHz)			
3300	14.07	15.5	-47.1
3450	13.84	14.9	-47.2
3600	13.10	14.8	-47.2

ITEH38009C6

Features

- High Efficiency and Linear Gain Operations
- Integrated ESD Protection
- Excellent thermal stability, low HCI drift

Suitable Applications

• All 4G/5G cellular application below 3.8GHz

- Large Positive and Negative Gate/Source Voltage Range for Improved Class C Operation
- Pb-free, RoHS-compliant

Table 1. Maximum Ratings

Rating	Symbol	Value	Unit
DrainSource Voltage	V _{DSS}	+65	Vdc
GateSource Voltage	V _{GS}	-10 to +10	Vdc
Operating Voltage	V_{DD}	+28	Vdc
Storage Temperature Range	Tstg	-65 to +150	°C
Case Operating Temperature	Tc	+150	°C
Operating Junction Temperature	T٦	+225	°C

Table 2. Thermal Characteristics

Characteristic	Symbol	Value	Unit
Thermal Resistance, Junction to Case	Do 10	2	°C/W
T _C = 85°C, T _J =200°C, DC test	R⊕JC	2	-0/00

Table 3. ESD Protection Characteristics

Test Methodology	Class
Human Body Model (per JESD22A114)	Class 2

Table 4. Electrical Characteristics (TA = 25 °C unless otherwise noted)

Characteristic	Symbol	Min	Тур	Max	Unit
DC Characteristics					
Drain-Source Voltage	\/		GE		V
V _{GS} =0, I _{DS} =100uA	$V_{(BR)DSS}$		65		V



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Zero Gate Voltage Drain Leakage Current	I _{pss}	 	1	μА
$(V_{DS} = 28V, V_{GS} = 0 V)$	1055			μιν
GateSource Leakage Current			4	
$(V_{GS} = 11 \text{ V}, V_{DS} = 0 \text{ V})$	Igss	 	I	μΑ
Gate Threshold Voltage	V _{GS} (th)	 2		V
$(V_{DS} = 28V, I_D = 600 \mu A)$	V _{GS} (In)	 2		V
Gate Quiescent Voltage	V	2.7		V
(V _{DD} = 28V, I _D = 70mA, Measured in Functional Test)	$V_{GS(Q)}$	 2.1		V

Load Mismatch (In Innogration Test Fixture, 50 ohm system): $V_{DD} = 28Vdc$, $I_{DQ} = 70$ mA, f = 3600 MHz

VSWR 10:1 at 9W pulse CW Output Power	No Device Degradation
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Figure 1:Pin Definition(Top View)



Pin No.	Symbol	Description
8,9,10,11	Vgs/RF In	Vgs and RF input
32,33,34,35	Vds/RF out	Vds and RF output
2,5,7,12,13,18,20,23,25,30,31,36	GND	DC/RF Ground
Others	NC	No connection
Package Base	GND	DC/RF Ground.



Reference Circuit of Test Fixture Assembly Diagram 3300-3600MHz RO4350B 20mils

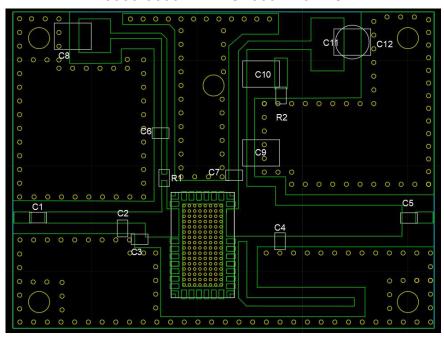


Figure 2. Test Circuit Component Layout

Table 5. Test Circuit Component Designations and Values

Component	Value	Quantity
U1	ITEH38009C6	1
C1、C5、C6、C7	8.2pF	4
C8、C9、C10、C11	10uF/63V	4
R1、R2	10 Ω	2
C12	470uF/63V	1
C2	1.2pF	1
C3	0.5pF	1
C4	1.8Pf	1



TYPICAL CHARACTERISTICS

Figure 3. ACPR Performance at 29dBm under 100MHz NR signal test

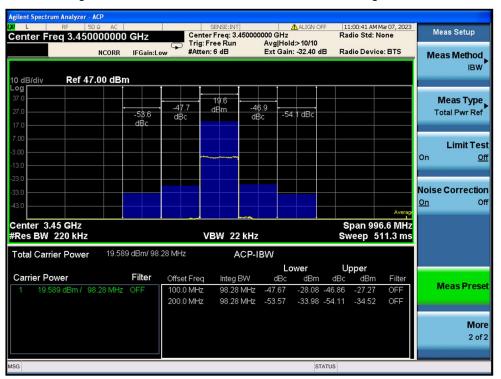
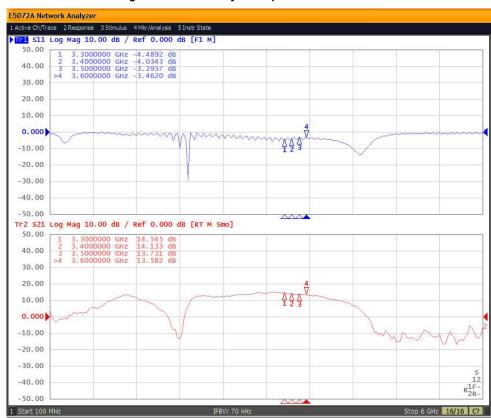
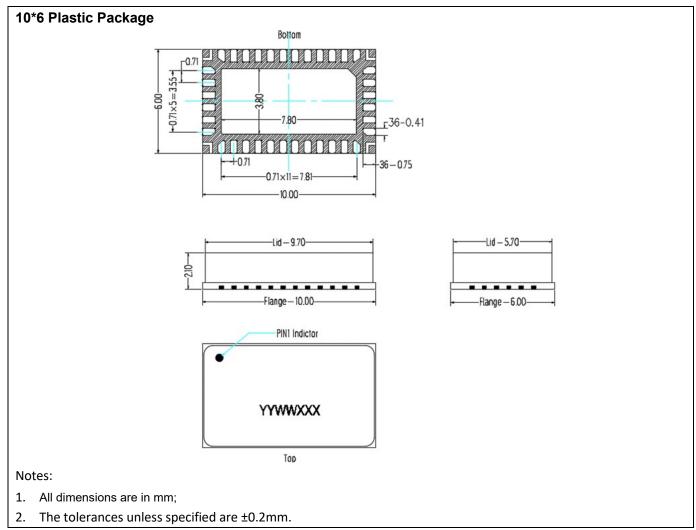


Figure 4.Network analyzer output S11/S21



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Revision history

Table 7. Document revision history

Date	Revision	Datasheet Status
2023/3/7	Rev 1.0	Preliminary Datasheet

Application data based on ZXY-23-03

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